

**In the Claims:**

1. (Currently Amended) A method of producing a silicon carbide ~~crystals~~ boule, comprising:

forcing nucleation sites of a silicon carbide seed crystal to a predefined pattern; and

growing the silicon carbide boule utilizing physical vapor transport (PVT) so as to provide selective preferential growth of silicon carbide corresponding to the predefined pattern.

2-10. Cancelled.

11. (Original) The method of Claim 1, wherein the forcing nucleation sites comprises forming a pattern on an exposed surface of the seed crystal so as to provide regions of the seed crystal which extend beyond other regions of the seed crystal.

12. (Original) The method of Claim 11, wherein the pattern comprises stripes in the seed crystal.

13. (Original) The method of Claim 11, wherein the pattern comprises a plurality of posts.

14. (Original) The method of Claim 13, wherein the posts are substantially circular.

15. (Original) The method of Claim 11, wherein the forming a pattern comprises forming a pattern of sidewalls in the exposed surface of the seed crystal.

16. (Original) The method of Claim 1, wherein forcing nucleation sites comprises forming a pattern of material other than silicon carbide on the silicon carbide seed crystal.

17. (Original) The method of Claim 16, wherein the pattern comprises stripes on the seed crystal.

18. (Original) The method of Claim 16, wherein the pattern comprises a plurality of posts on the seed crystal.

19. (Currently Amended) The method of Claim 16, wherein the pattern comprises a layer of material having a plurality of ~~opening~~ openings therein so as to expose ~~potions~~ portions of the seed crystal.

20. (Original) The method of Claim 19, wherein the openings are substantially circular.

21. (Original) The method of Claim 16, wherein the material other than silicon carbide comprises graphite.

22. (Currently Amended) The method of Claim 16, wherein the pattern of material other than silicon carbide provides a pattern of regions ~~of~~ having a reduced sticking coefficient over other regions of the seed crystal.

23-54. Cancelled.

55. (New) A method of producing a silicon carbide boule, comprising:  
forcing nucleation sites of a single silicon carbide seed crystal to a predefined pattern; and

growing the silicon carbide boule utilizing physical vapor transport (PVT) so as to provide selective preferential growth of silicon carbide on the silicon carbide seed crystal corresponding to the predefined pattern so as to provide a single crystal silicon carbide boule.

56. (New) The method of Claim 55, wherein the forcing nucleation sites comprises forming a pattern on an exposed surface of the single silicon carbide seed crystal so as to provide regions of the silicon carbide seed crystal which extend beyond other regions of the silicon carbide seed crystal.